



# MT6010

## 60V N-Channel MOSFET

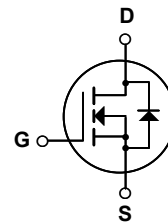
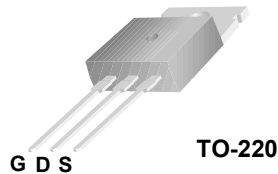
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Mos-tech's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as automotive, DC/DC converters, and high efficiency switching for power management in portable and battery operated products.

### Features

- 15A, 60V,  $R_{DS(on)} = 0.04\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 11.5 nC)
- Low Crss ( typical 25 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	MT6010	Units
V <sub>DSS</sub>	Drain-Source Voltage	60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	15	A
		10.1	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	50	A
V <sub>GSS</sub>	Gate-Source Voltage	± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	105	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	20	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	5.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	53	W
		0.35	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	2.85	°C/W
R <sub>θCS</sub>	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.07	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 48\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	--	0.03	0.05	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 25\text{ V}, I_D = 10\text{ A}$ (Note 4)	--	12	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	480	590	pF
$C_{oss}$	Output Capacitance		--	170	220	pF
$C_{rss}$	Reverse Transfer Capacitance		--	25	35	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 10\text{ A},$ $R_G = 25\ \Omega$	--	5	20	ns	
$t_r$	Turn-On Rise Time		--	45	100	ns	
$t_{d(off)}$	Turn-Off Delay Time		--	20	50	ns	
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	25	60	ns
$Q_g$	Total Gate Charge		$V_{DS} = 48\text{ V}, I_D = 10\text{ A},$ $V_{GS} = 10\text{ V}$	--	11.5	15	nC
$Q_{gs}$	Gate-Source Charge	(Note 4, 5)	--	3	--	nC	
$Q_{gd}$	Gate-Drain Charge		--	4.5	--	nC	

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	15	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	80	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 10\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	43	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	50	--	nC

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 450\ \mu\text{H}, I_{AS} = 10\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 20\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

# Typical Characteristics

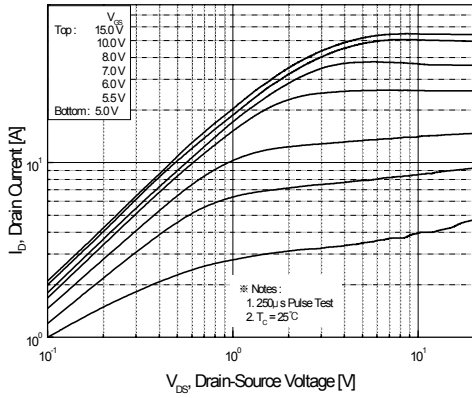


Figure 1. On-Region Characteristics

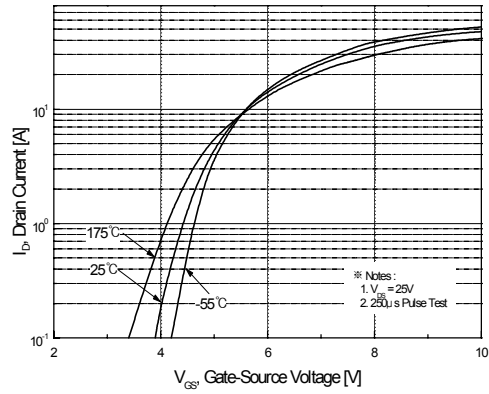


Figure 2. Transfer Characteristics

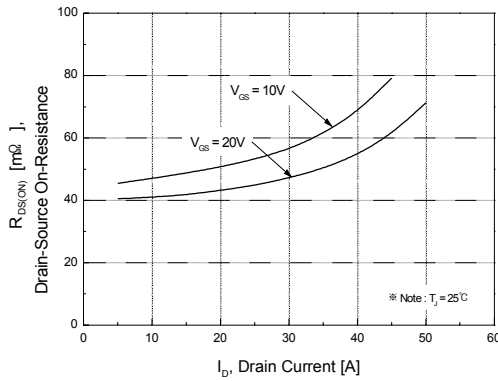


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

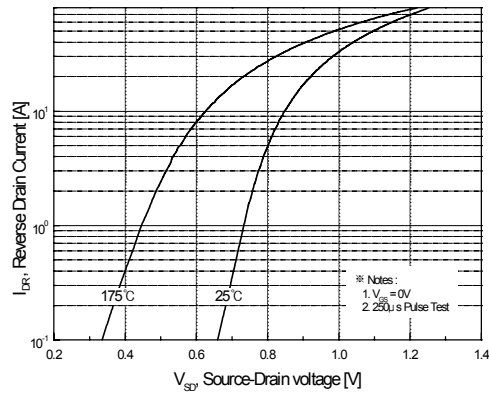


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

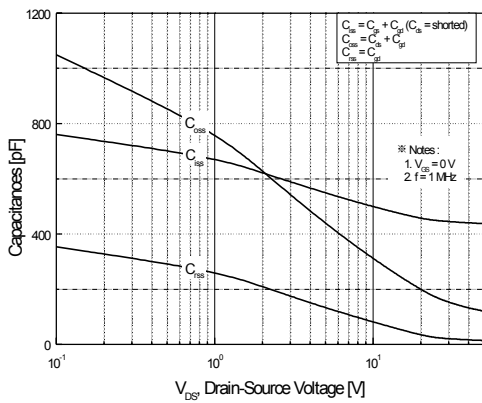


Figure 5. Capacitance Characteristics

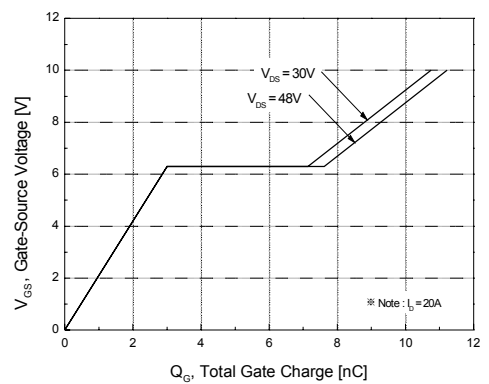


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

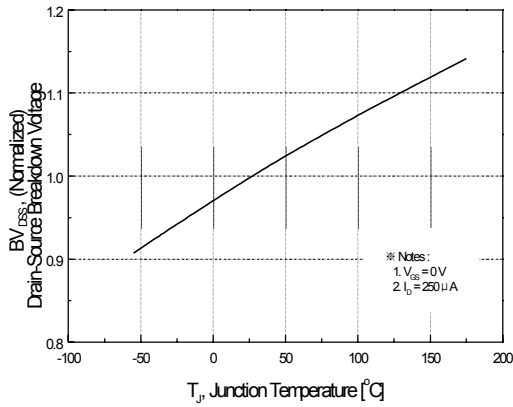


Figure 7. Breakdown Voltage Variation vs. Temperature

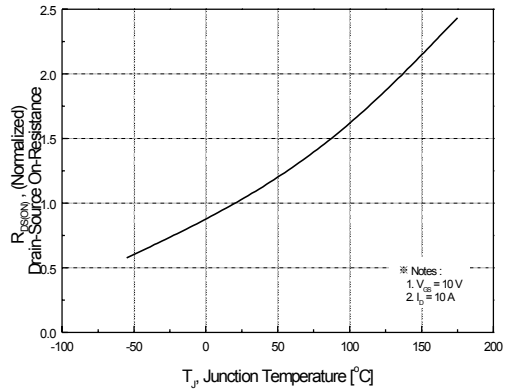


Figure 8. On-Resistance Variation vs. Temperature

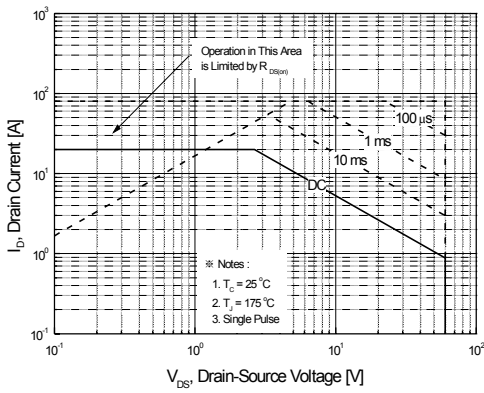


Figure 9. Maximum Safe Operating Area

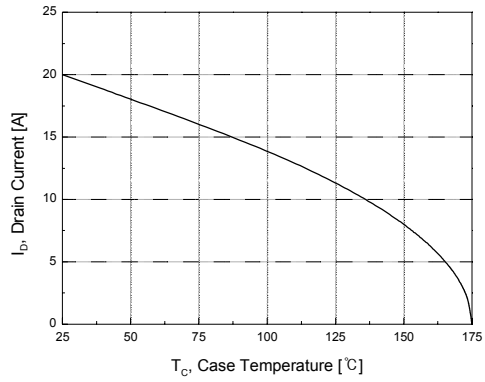


Figure 10. Maximum Drain Current v.s Case Temperature

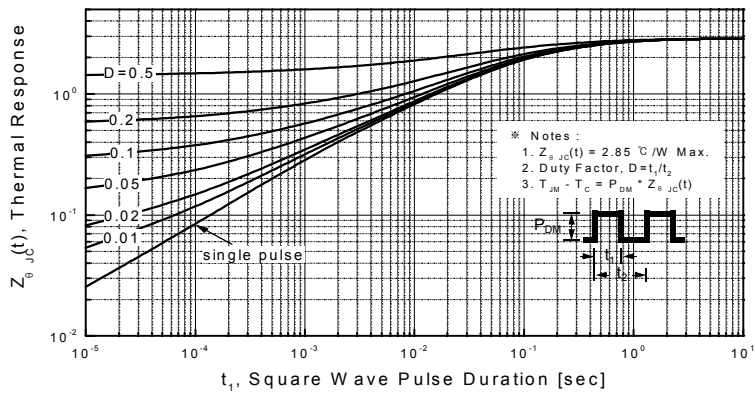
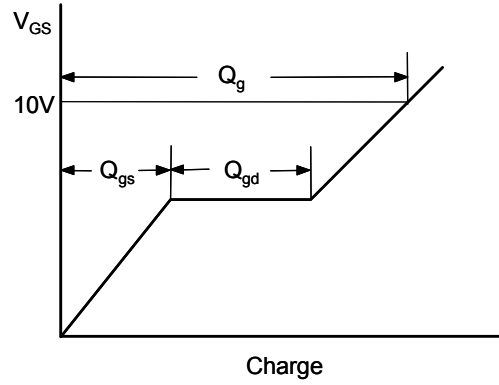
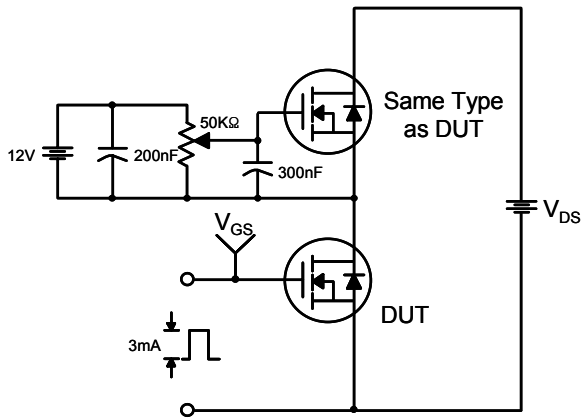
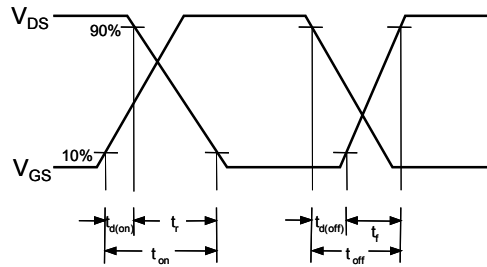
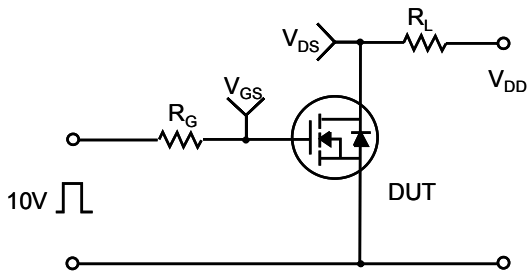


Figure 11. Transient Thermal Response Curve

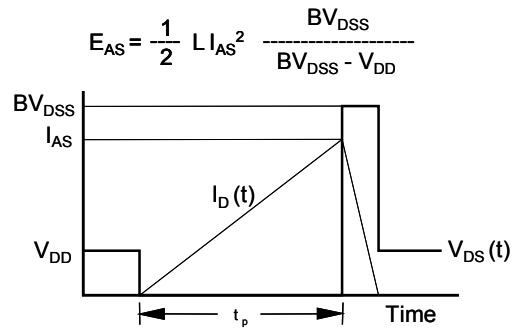
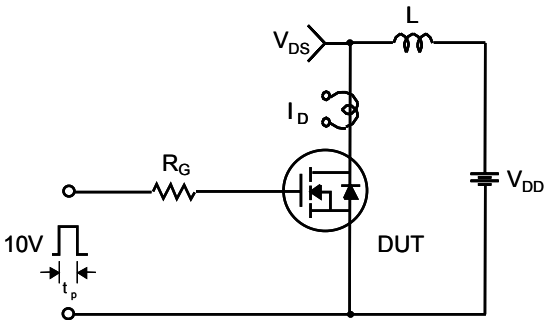
**Gate Charge Test Circuit & Waveform**



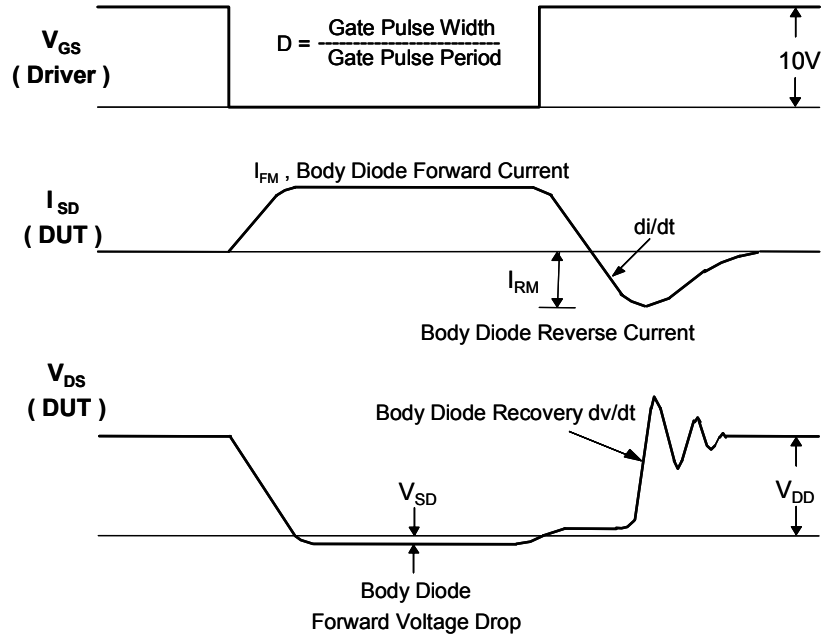
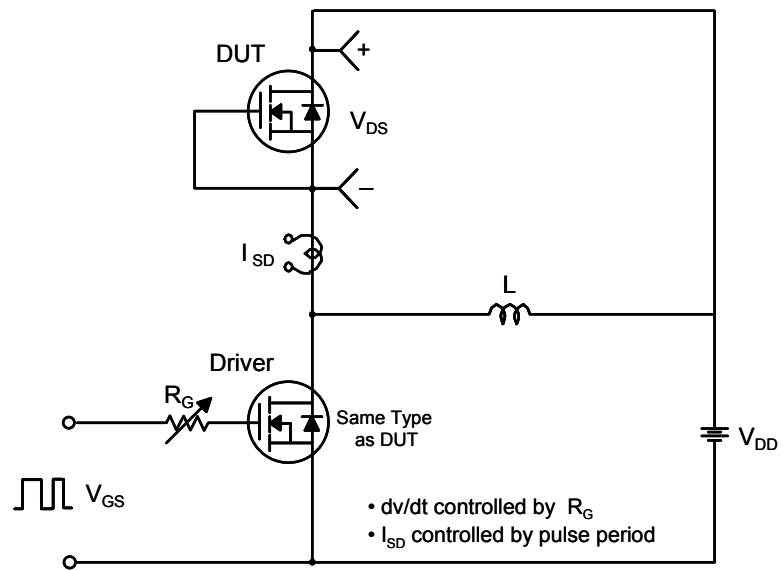
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**



Peak Diode Recovery dv/dt Test Circuit & Waveforms



# TO-220

